

Abstract

A memory array for a magneto-resistive memory device is provided. The array includes a plurality of memory cells disposed in rows and columns in the memory array. Each memory cell is paired with another memory cell such that the pair of memory cells are driven to first and second, different states by the same signals. A sense point for reading data from a pair of memory cells is also provided. The sense point is located at a point with one of the memory cells of each pair on one side of the sense point and the other memory cell of each pair located on the other side of the sense point.